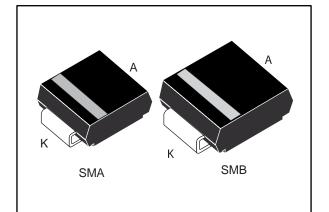


## Automotive ultrafast recovery diode

Datasheet - production data



### Features

- AEC-Q101 qualified
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature
- ECOPACK®2 compliant component

### Description

This device that uses ST's new 400 V planar Pt doping technology, is specially suited for switching mode base drive and transistor circuits.

Packaged in SMB and SMA, it is intended for use in low voltage, high frequency inverters, freewheeling and polarity protection in automotive applications.

### Table 1: Device summary

Symbol	Value
lf(AV)	1 A
V <sub>RRM</sub>	400 V
Tj (max.)	175 °C
V <sub>F</sub> (typ.)	0.9 V
t <sub>rr</sub> (typ.)	14 ns

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www.st.com

This is information on a product in full production.

## 1 Characteristics

Table 2: Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)

Symbol	Parame	Value	Unit		
Vrrm	Repetitive peak reverse voltage $T_j = -40 \degree C$ to +175 $\degree C$		T <sub>j</sub> = -40 °C to +175 °C	400	V
1	Average forward current,		t, SMA T <sub>I</sub> = 130 °C		٨
IF(AV)	$\delta$ = 0.5, square wave	SMB	T <sub>I</sub> = 140 °C	1.0	A
	FSM Surge non repetitive forward current		t <sub>p</sub> = 10 ms sinusoidal	30	٨
IFSM			t <sub>p</sub> = 8.3 ms sinusoidal	37	A
T <sub>stg</sub>	Storage temperature range			-65 to +175	°C
Tj	Operating junction temperature <sup>(1)</sup>			-40 to +175	°C

#### Notes:

 $^{(1)}(dP_{tot}/dT_j) < (1/R_{th(j-a)})$  condition to avoid thermal runaway for a diode on its own heatsink.

Table 3: Therm	al resistance parameters
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Symbol	Parameter	Maximum value	Unit	
<b>_</b>		SMA	30	°C ///
R <sub>th(j-l)</sub> Junction to lead		SMB	25	°C/W

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
L (1)			., .,	-		5	۵
IR <sup>(1)</sup> Reverse leak	Reverse leakage current	T <sub>j</sub> = 125 °C	Vr = Vrrm	-	5	50	μA
		T <sub>j</sub> = 25 °C		-	1.30	1.60	
VF <sup>(2)</sup>	Forward voltage drop	T <sub>j</sub> = 100 °C	I <sub>F</sub> = 1 A	-	1.05	1.30	V
		T <sub>j</sub> = 150 °C		-	0.90	1.15	

#### Table 4: Static electrical characteristics ( per diode)

#### Notes:

 $^{(1)} Pulse test: t_p$  = 5 ms,  $\delta$  < 2%  $^{(2)} Pulse test: t_p$  = 380 µs,  $\delta$  < 2%

To evaluate the conduction losses, use the following equation:

 $P = 0.9 \ x \ I_{F(AV)} + 0.250 \ x \ I_{F^2(RMS)}$ 



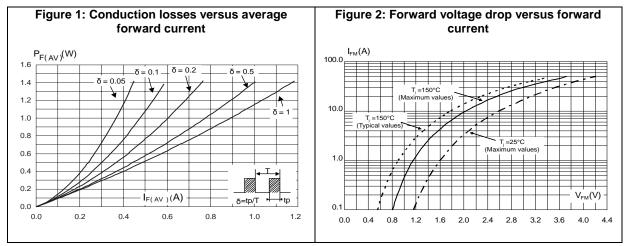
### Characteristics

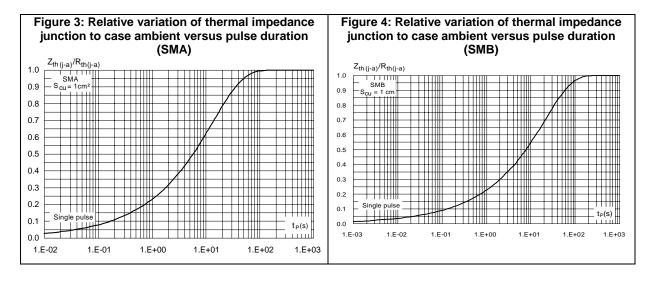
Symbol	Parameters	Test conditions	Min.	Тур.	Max.	Unit
		I <sub>F</sub> = 1 A dI <sub>F</sub> /dt = -50 A/μs V <sub>R</sub> = 30 V	-		30	20
t <sub>rr</sub> Reverse recovery time	I <sub>F</sub> = 1 A dI <sub>F</sub> /dt = -100 A/μs V <sub>R</sub> = 30 V	-	14	20	ns	
Irm	Reverse recovery current	$I_{F} = 1 A dI_{F}/dt = -200 A/\mu s V_{R} = 320 V T_{j} = 125 °C$	-	2.5	3.5	A
V <sub>FP</sub>	Forward recovery voltage	l <sub>F</sub> = 1 A dl <sub>F</sub> /dt = 100 A/μs	-	2.9		V
t <sub>fr</sub>	Forward recovery time	I <sub>F</sub> = 1 A dI <sub>F</sub> /dt = 100 A/µs V <sub>FR</sub> = 1.1 x V <sub>F</sub> (max)	-		50	ns

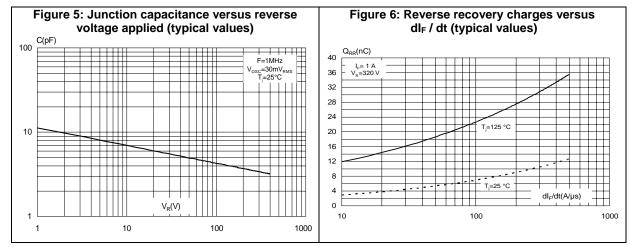
Table 5: Dvnamic electrical characteristics per diode (T<sub>i</sub> = 25 °C, unless otherwise specified)



### 1.1 Characteristics (curves)



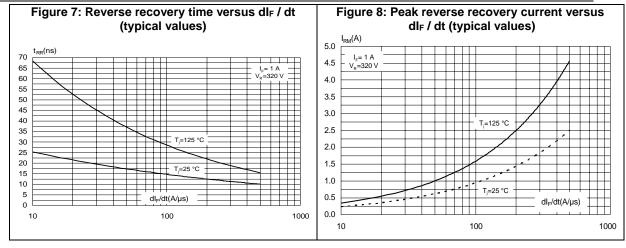


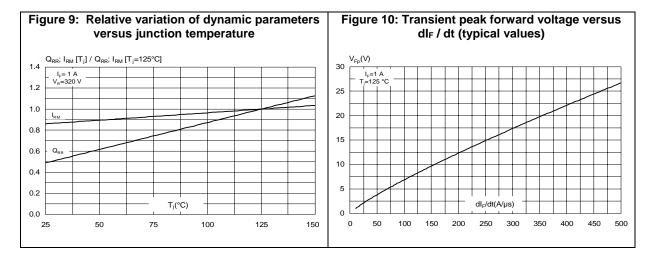


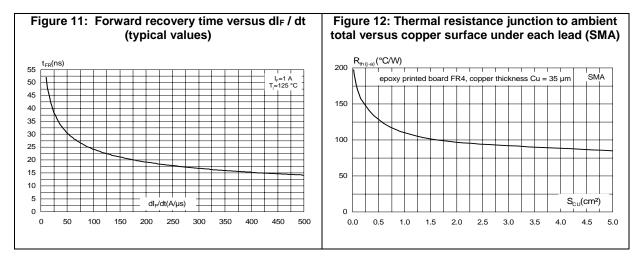
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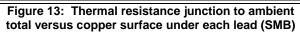
#### **Characteristics**

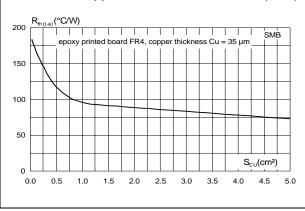






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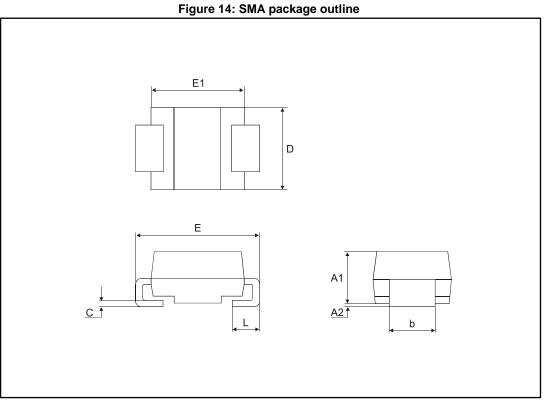




## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: *www.st.com*. ECOPACK<sup>®</sup> is an ST trademark.

### 2.1 SMA package information



### Table 6: SMA package mechanical data

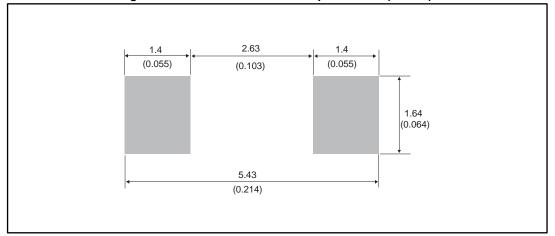
Dimensions					
Ref.	Millir	neters	Inches		
	Min.	Max.	Min.	Max.	
A1	1.90	2.45	0.075	0.097	
A2	0.05	0.20	0.002	0.008	
b	1.25	1.65	0.049	0.065	
с	0.15	0.40	0.006	0.016	
D	2.25	2.90	0.089	0.114	
E	4.80	5.35	0.189	0.211	
E1	3.95	4.60	0.156	0.181	
L	0.75	1.50	0.030	0.059	



### Package information

#### Figure 15: SMA recommended footprint in mm (inches)

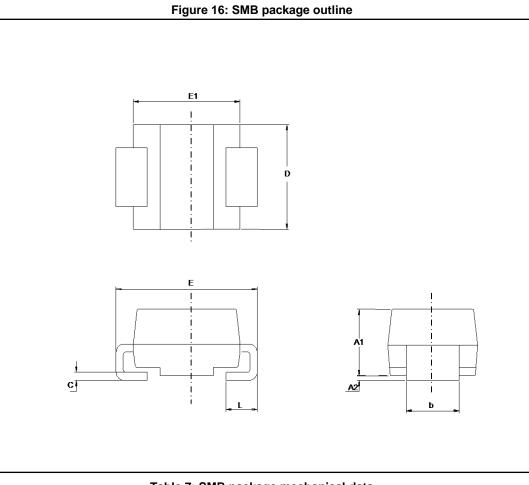
### STTH1R04-Y



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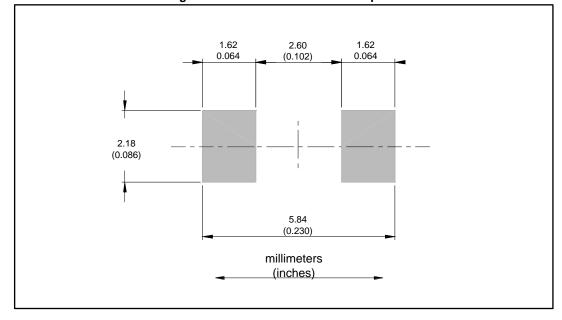
### 2.2 SMB package information



	Dimensions					
Ref.	Millimeters		Incl	hes		
	Min.	Max.	Min.	Max.		
A1	1.90	2.45	0.0748	0.0965		
A2	0.05	0.20	0.0020	0.0079		
b	1.95	2.20	0.0768	0.0867		
с	0.15	0.40	0.0059	0.0157		
D	3.30	3.95	0.1299	0.1556		
E	5.10	5.60	0.2008	0.2205		
E1	4.05	4.60	0.1594	0.1811		
L	0.75	1.50	0.0295	0.0591		



### Figure 17: SMB recommended Footprint



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## **3** Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
STTH1R04AY	HR4Y	SMA	0.068 g	5000	Tape and reel
STTH1R04UY	BR4Y	SMB	0.12 g	2500	Tape and reel

### Table 8: Ordering information

## 4 Revision history

### Table 9: Document revision history

Date	Revis ion	Changes
09-Jul-2013	1	First issue
16-Mar-2017	2	Updated Table 2: "Absolute ratings (limiting values per diode at 25 °C, unless otherwise specified)".



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